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Vishay Semiconductors

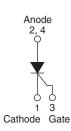
RoHS

COMPLIANT

HALOGEN FREE

## Thyristor, Surface Mount, Phase Control SCR, 16 A





PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub>	16 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V						
$V_{TM}$	1.25 V						
I <sub>GT</sub>	45 mA						
$T_J$	-40 to +125 °C						
Package	D <sup>2</sup> PAK (TO-263AB)						
Circuit configuration	Single SCR						

#### **FEATURES**

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

### **APPLICATIONS**

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

### **DESCRIPTION**

The VS-25TTS12SLHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5							
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	8.5	13.5	А						
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	16.5	25.0							

#### Note

•  $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	16	۸					
I <sub>RMS</sub>		25	A					
V <sub>RRM</sub> /V <sub>DRM</sub>		1200	V					
I <sub>TSM</sub>		350	Α					
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V					
dV/dt		500	V/µs					
dl/dt		150	A/µs					
T <sub>J</sub>		-40 to +125	°C					

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> / I <sub>DRM</sub> , AT 125 °C mA					
VS-25TTS12SLHM3	1200	1200	10					



PARAMETER	SYMBOL	TEG	VAL	UES	LINUTO	
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP. MAX.		UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° c	T <sub>C</sub> = 93 °C, 180° conduction half sine wave			
Maximum RMS on-state current	I <sub>RMS</sub>			2	5	Α
Maximum peak, one-cycle,		10 ms sine pulse,	rated V <sub>RRM</sub> applied	30	00	_ ^
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse,	no voltage reapplied	3	50	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse,	rated V <sub>RRM</sub> applied	4	50	A <sup>2</sup> s
Maximum i-t for fusing	1-1	10 ms sine pulse,	630		A-8	
Maximum $I^2\sqrt{t}$ for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied			00	A²√s
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C			25	V
On-state slope resistance	r <sub>t</sub>	T <sub>J</sub> = 125 °C		12.0		mΩ
Threshold voltage	V <sub>T(TO)</sub>	TJ= 125 C		1.0		V
Maximum reverse and direct leakage current	1 /1	T <sub>J</sub> = 25 °C	V - Patad V A/	0	.5	
Maximum reverse and direct leakage current	I <sub>RM</sub> / I <sub>DM</sub>	T <sub>J</sub> = 125 °C	V <sub>R</sub> = Rated V <sub>RRM</sub> /V <sub>DRM</sub>	10		
Holding current	I <sub>H</sub>	$ \begin{array}{c} \text{VS-25TTS08,} \\ \text{VS-25TTS12} \end{array} \qquad \begin{array}{c} \text{Anode supply} = 6 \text{ V,} \\ \text{resistive load, initial } I_T = 1 \text{ A,} \\ T_J = 25 ^{\circ}\text{C} \end{array} $		-	150	mA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C			00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$			500	
Maximum rate of rise of turned-on current	di/dt				150	

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P <sub>GM</sub>		8.0	W				
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV				
Maximum peak positive gate current	+I <sub>GM</sub>		1.5	Α				
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V				
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J$ = -10 °C	60	mA				
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J$ = 25 °C	45					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20					
		Anode supply = 6 V, resistive load, $T_J$ = -10 °C	2.5					
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C 2.		v				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V				
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V reted value	0.25					
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value	2.0	mA				

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9					
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.I</sub> = 125 °C	4	μs				
Typical turn-off time	t <sub>q</sub>	1J = 125	110					

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C				
Soldering temperature T <sub>S</sub>		For 10 s (1.6 mm from case)	260					
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.1	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> (1)		40	C/VV				
Approximate weight			2	g				
Approximate weight			0.07	OZ.				
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	25TTS	S12SH				

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm] copper 40 °C/W

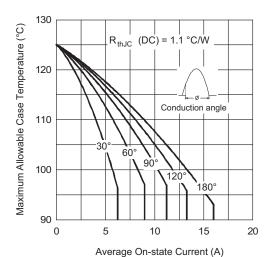


Fig. 1 - Current Rating Characteristics

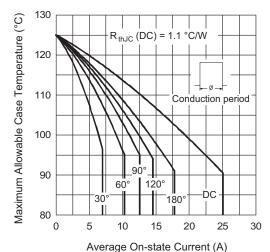


Fig. 2 - Current Rating Characteristics

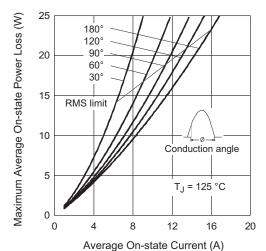


Fig. 3 - On-State Power Loss Characteristics

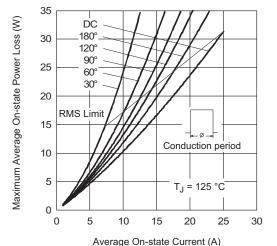


Fig. 4 - On-State Power Loss Characteristics

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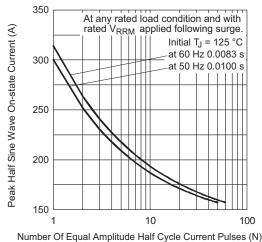


Fig. 5 - Maximum Non-Repetitive Surge Current

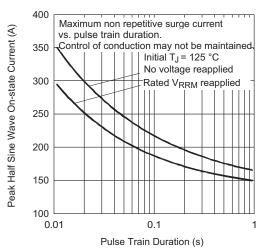


Fig. 6 - Maximum Non-Repetitive Surge Current

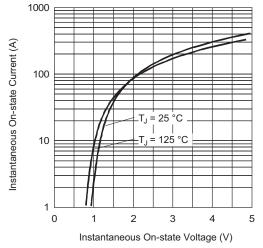


Fig. 7 - On-State Voltage Drop Characteristics

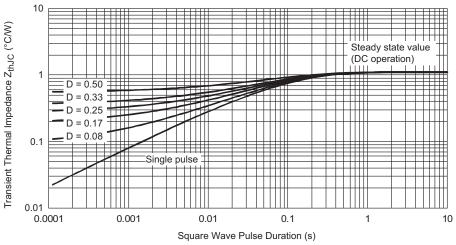


Fig. 8 - Gate Characteristics

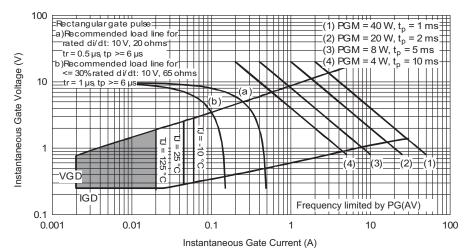
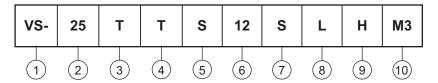


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

### **ORDERING INFORMATION TABLE**

### Device code



- Vishay Semiconductors product
- 2 Current rating (25 = 25 A)
- Gircuit configuration:
  T = single thyristor
- 4 Package:

 $T = D^2PAK (TO-263AB)$ 

- 5 Type of silicon:
  - S = standard recovery rectifier
- 6 Voltage rating: voltage code x 100 = V<sub>RRM</sub> 12 = 1200 V
- 7 S = surface mountable
- L = tape and reel (left oriented), for different orientation contact factory
- H = AEC-Q101 qualified
- M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

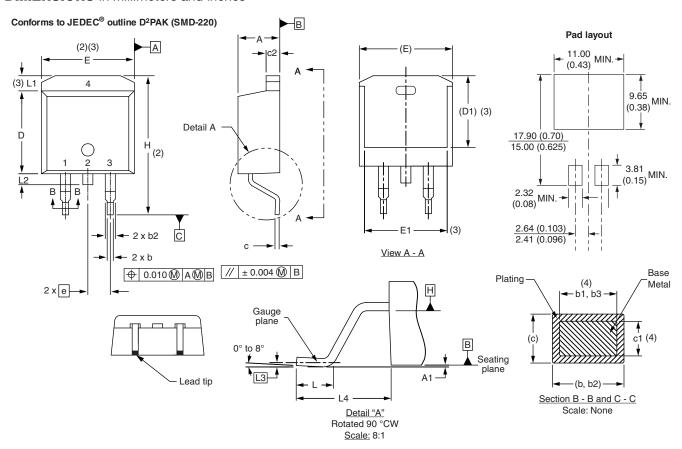
ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-25TTS12SLHM3	800	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95046				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96317				



### D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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